TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC257AP, TC74HC257AF, TC74HC257AFN

QUAD 2 - CHANNEL MULTIPLEXER (3 - STATE)

The TC74HC257A is high speed CMOS MULTIPLEXER fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

It is composed of four independent 2 - channel multiplexers with common SELECT and $\overline{OUTPUTENABLE}$ (\overline{OE}).

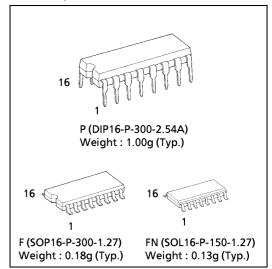
If \overline{OE} is set low, the outputs are held in a high-impedance state. When SELECT is set low, "A" data inputs are enabled. Conversely, when SELECT is high, "B" data inputs are enabled.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

- High Speed······ t_{pd} = 10ns(typ.) at V_{CC} = 5V
- Low Power Dissipation $I_{CC} = 4\mu A(Max.)$ at $Ta = 25^{\circ}C$
- High Noise Immunity......V_{NIH} = V_{NIL} = 28% V_{CC} (Min.)
- Output Drive Capability 15 LSTTL Loads
- Symmetrical Output Impedance... | I_{OH} | = I_{OL} = 6mA(Min.)
- Balanced Propagation Delays $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range ···· V_{CC} (opr.) = 2V~6V
- Pin and Function Compatible with 74LS257

(Note) The JEDEC SOP (FN) is not available in Japan.



PIN ASSIGNMENT SELECT 1 16 V_{CC} 1A 2 15 OE 1B 3 4A 1Y 4 **4B** 13 2A 5 12 4Y 2B 6 3A 11 2Y 7 10 3B GND 8 3Y (TOP VIEW)

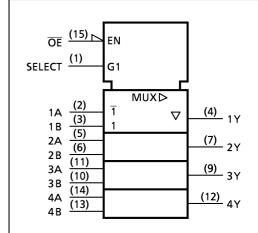
TRUTH TABLE

	INPL	OUTPUT		
ŌĒ	SELECT	Α	В	Y
Н	Х	Х	Х	Z
L	L	L	Х	L
L	L	Н	Х	Н
L	Н	Х	L	L
L	Н	Х	Н	Н

X : Don't Care Z : High Impedance

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IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	− 0.5~7	V
DC Input Voltage	V _{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V _{OUT}	−0.5~V _{CC} + 0.5	V
Input Diode Current	I _{IK}	± 20	mA
Output Diode Current	I _{OK}	± 20	mA
DC Output Current	I _{OUT}	±35	mA
DC V _{CC} / Ground Current	I _{cc}	± 75	mA
Power Dissipation	P _D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T _{stg}	−65~150	°C

*500mW in the range of Ta= $-40^{\circ}\text{C}\sim65^{\circ}\text{C}$. From Ta=65°C to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V _{cc}	2~6	V
Input Voltage	V _{IN}	0~V _{cc}	V
Output Voltage	V _{OUT}	0~V _{cc}	V
Operating Temperature	T _{opr}	−40~85	°C
Input Rise and Fall Time	t _r , t _f	$0 \sim 1000 (V_{CC} = 2.0V)$ $0 \sim 500 (V_{CC} = 4.5V)$ $0 \sim 400 (V_{CC} = 6.0V)$	ns

DC ELECTRICAL CHARACTERISTICS

	CVARDOL	TEST CO	MDITION	V _{cc}	Ta = 25°C			$Ta = -40 \sim 85^{\circ}C$		LINUT
PARAMETER	SYMBOL	TEST CONDITION		(V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High - Level Input Voltage	VIH			2.0 4.5 6.0	1.50 3.15 4.20	111	_ _ _	1.50 3.15 4.20	_ _ _	V
Low - Level Input Voltage	VIL			2.0 4.5 6.0	_ _ _	_ _ _	0.50 1.35 1.80	=	0.50 1.35 1.80	V
High - Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	_ _ _	1.9 4.4 5.9	_ _	v
Oŭtput Voltage			$I_{OH} = -6mA$ $I_{OH} = -7.8mA$	4.5 6.0	4.18 5.68	4.31 5.80	=	4.13 5.63	=	
Low - Level Output Voltage	V_{OL} $V_{IN} = V_{IH} \text{ or } V_{IL}$	V _{I N} =	$I_{OL} = 20 \mu A$	2.0 4.5 6.0	_ _ _	0.0 0.0 0.0	0.1 0.1 0.1	_ _	0.1 0.1 0.1	v
		V _{IH} or V _{IL}	$I_{OL} = 6mA$ $I_{OL} = 7.8mA$	4.5 6.0	_	0.17 0.18	0.26 0.26	=	0.33 0.33	
3 - State Off Leak Current	l _{oz}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		6.0	_	_	±0.5	_	± 5.0	
Input Leakage Current	I _{IN}	$V_{IN} = V_{CC}$ or GND		6.0	_	_	± 0.1	_	± 1.0	μA
Quiescent Supply Current	I _{CC}	$V_{IN} = V_{CC}$ or GND		6.0	_	_	4.0	_	40.0	

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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$)

	SYMBOL TEST CONDITION		CL	V _{CC}	-	a = 25°C		Ta = − 40~85°C		UNIT
PARAMETER	SAIMBOL	TEST CONDITION	(pF)	(V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH}		50	2.0 4.5 6.0	_ _ _	20 6 5	60 12 10	_ _ _	75 15 13	
Propagation Delay Time	t _{pLH}		50	2.0 4.5 6.0	_ _ _	45 13 11	100 20 17	_ _ _	125 25 21	
$(A, B-Y, \overline{Y})$	t _{pHL}		150	2.0 4.5 6.0	_ _ _	62 18 15	140 28 24	_ _ _	175 35 30	
Propagation Delay Time	t _{pLH}		50	2.0 4.5 6.0	_ _ _	45 13 11	100 20 17	_ _ _	125 25 21	ns
(SELECT $= Y, \overline{Y}$)	t _{pHL}		150	2.0 4.5 6.0	_ _ _	62 18 15	140 28 24	_ _ _	175 35 30	113
3 — State Output	t _{pZL}		50	2.0 4.5 6.0	_ _ _	40 12 10	110 22 19	_ _ _	140 28 24	
Enable Time	t _{pZH}	$R_L = 1k\Omega$	150	2.0 4.5 6.0	3.4	57 17 14	150 30 26	_ _ _	190 38 33	
3 — State Output Enable Time	t _{pLZ} t _{pHZ}	$R_L = 1k\Omega$	50	2.0 4.5 6.0	18 -40	28 14 13	140 28 24	_ _ _	175 35 30	
Input Capacitance	C _{IN}		13	-	O ÷ 2.	5	10	_	10	
Output Capacitance	C _{OUT}			0	_	10	_	_	_	pF
Power Dissipation Capacitance	C _{PD} (1)				_	47	_	_	_	Α.

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

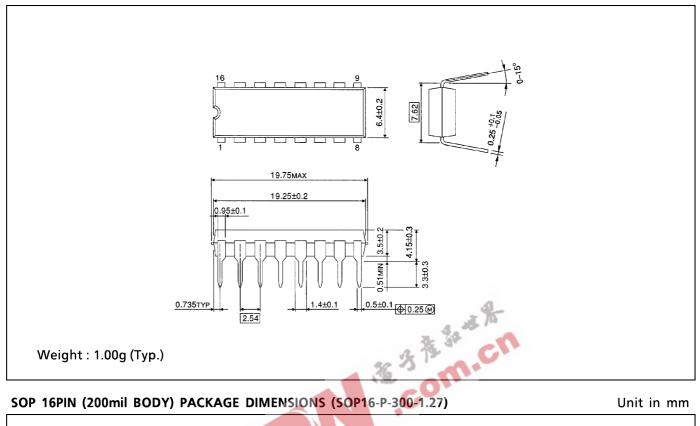
Average operating current can be obtained by the equation:

 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4$ (per bit)

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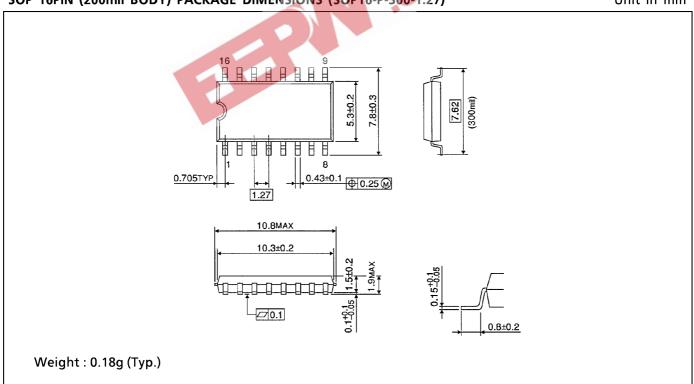
DIP 16PIN PACKAGE DIMENSIONS (DIP16-P-300-2.54A)

Unit in mm



SOP 16PIN (200mil BODY) PACKAGE DIMENSIONS (SOP16-P-300-1.27)

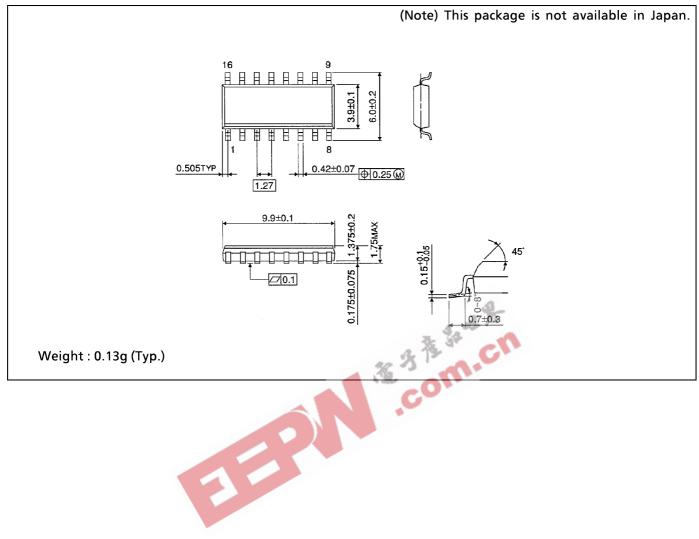
Unit in mm



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SOP 16PIN (150mil BODY) PACKAGE DIMENSIONS (SOL16-P-150 -1.27)

Unit in mm



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